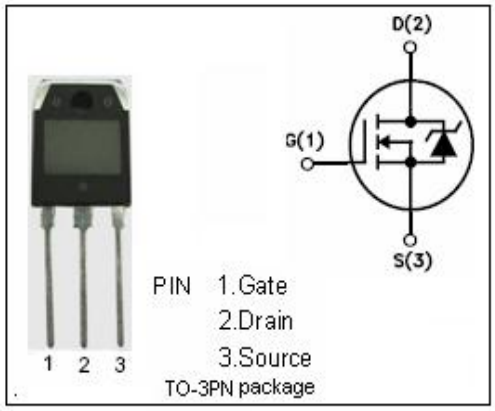
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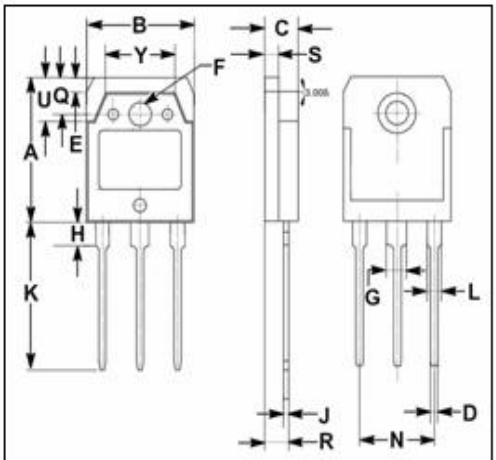


DESCRIPTION

- Drain Current –I_D=10A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 450V(Min)

APPLICATIONS

- high voltage, high speed power switching



DIM	mm MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	450	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	10	A
P_{tot}	Total Dissipation@TC=25℃	100	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.25	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	35	℃/W

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	450			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=1mA	2.5	3.5	5.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	V_{GS}=10V; I_D= 5A		0.5	0.65	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 450V; V_{GS}= 0			500	uA
V_{SD}	Forward On-Voltage	I_S=10A; V_{GS}=0		1.1	1.5	V
tr	Rise time	VGS=10V;ID=10A; RL=25Ω		80	120	ns
ton	Turn-on time			110	165	ns
tf	Fall time			80	120	ns
toff	Turn-off time			240	360	ns

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